

IRLB8721PbF

HEXFET® Power MOSFET

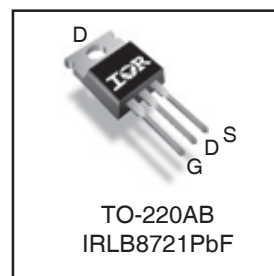
Applications

- Optimized for UPS/Inverter Applications
- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use

V _{DSS}	R _{DS(on)} max	Qg (typ.)
30V	8.7mΩ @ V _{GS} = 10V	7.6nC

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

	Parameter	Max.	Units		
V _{DS}	Drain-to-Source Voltage	30	V		
V _{GS}	Gate-to-Source Voltage	± 20			
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	62	A		
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	44			
I _{DM}	Pulsed Drain Current ①	250			
P _D @ T _C = 25°C	Maximum Power Dissipation ⑤	65	W		
P _D @ T _C = 100°C	Maximum Power Dissipation ⑤	33			
	Linear Derating Factor	0.43	W/°C		
T _J	Operating Junction and Storage Temperature Range	-55 to + 175	°C		
T _{STG}					
				Soldering Temperature, for 10 seconds	300 (1.6mm from case)
				Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑤	—	2.3	°C/W
R _{θCS}	Case-to-Sink, Flat Greased Surface	0.5	—	
R _{θJA}	Junction-to-Ambient ④	—	62	

Notes ① through ⑤ are on page 9
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Static @ T_J = 25°C (unless otherwise specified)

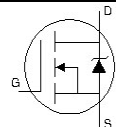
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	21	—	mV/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	6.5	8.7	mΩ	V _{GS} = 10V, I _D = 31A ③
		—	13.1	16		V _{GS} = 4.5V, I _D = 25A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	1.80	2.35	V	V _{DS} = V _{GS} , I _D = 25μA
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-7.0	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	35	—	—	S	V _{DS} = 15V, I _D = 25A
Q _g	Total Gate Charge	—	7.6	13	nC	V _{DS} = 15V V _{GS} = 4.5V I _D = 25A See Fig. 16
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	1.9	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.2	—		
Q _{gd}	Gate-to-Drain Charge	—	3.4	—		
Q _{godr}	Gate Charge Overdrive	—	2.0	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	4.6	—		
Q _{oss}	Output Charge	—	7.9	—	nC	V _{DS} = 15V, V _{GS} = 0V
R _G	Gate Resistance	—	2.3	3.8	Ω	
t _{d(on)}	Turn-On Delay Time	—	9.1	—	ns	V _{DD} = 15V, V _{GS} = 4.5V ③ I _D = 25A R _G = 1.8Ω See Fig. 14
t _r	Rise Time	—	93	—		
t _{d(off)}	Turn-Off Delay Time	—	9.0	—		
t _f	Fall Time	—	17	—		
C _{iss}	Input Capacitance	—	1077	—	pF	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz
C _{oss}	Output Capacitance	—	360	—		
C _{rss}	Reverse Transfer Capacitance	—	110	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	98	mJ
I _{AR}	Avalanche Current ①	—	25	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	62	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	250		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 25A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	16	24	ns	T _J = 25°C, I _F = 25A, V _{DD} = 15V
Q _{rr}	Reverse Recovery Charge	—	14	21	nC	di/dt = 200A/μs ③



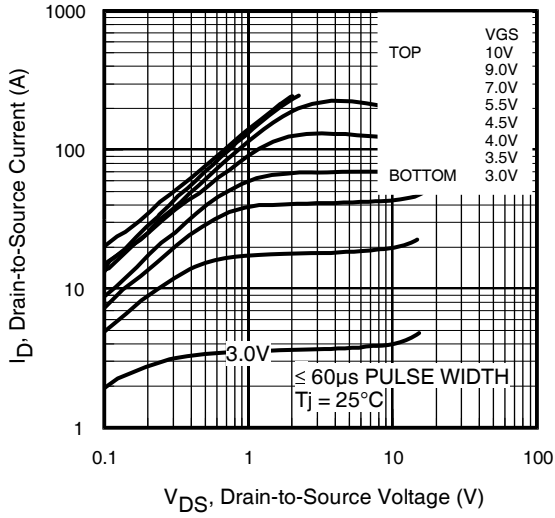


Fig 1. Typical Output Characteristics

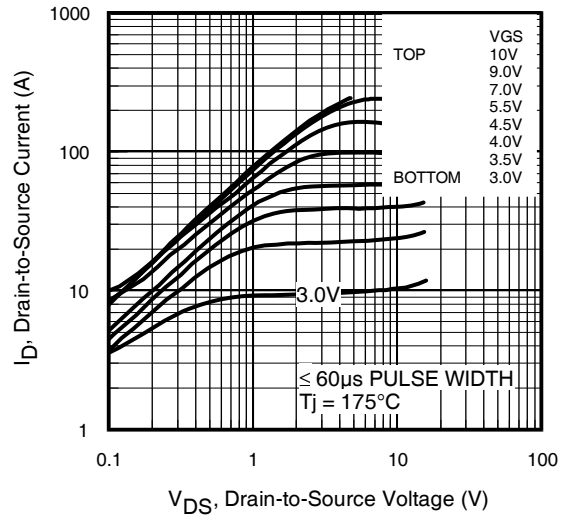


Fig 2. Typical Output Characteristics

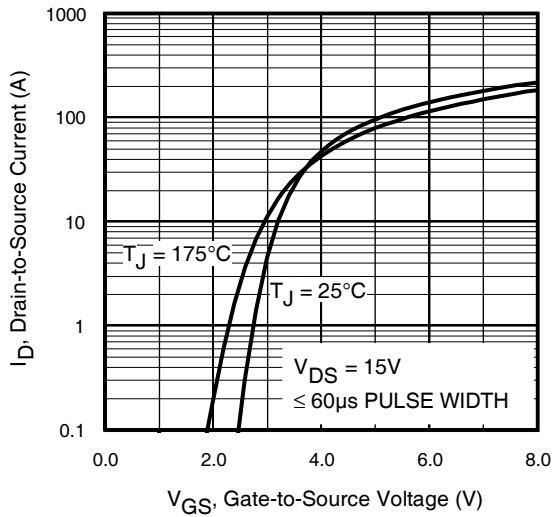


Fig 3. Typical Transfer Characteristics

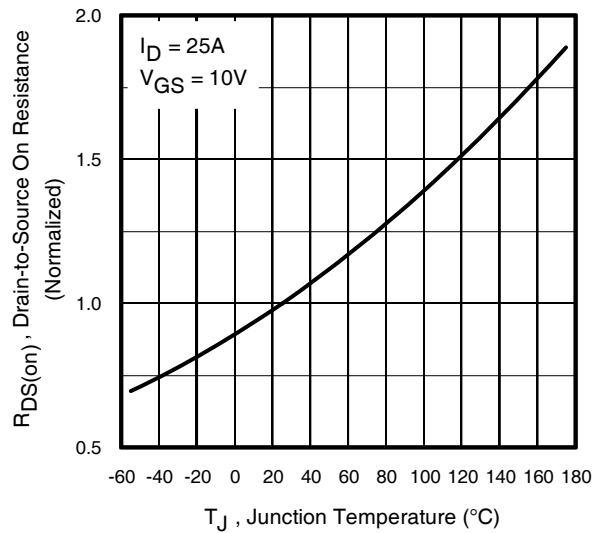


Fig 4. Normalized On-Resistance vs. Temperature

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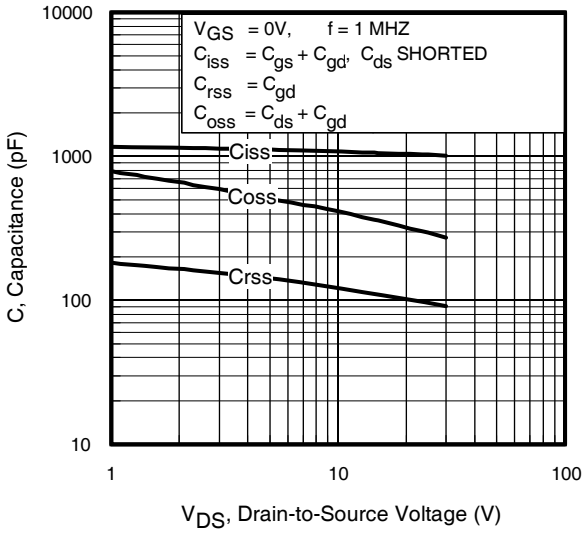


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

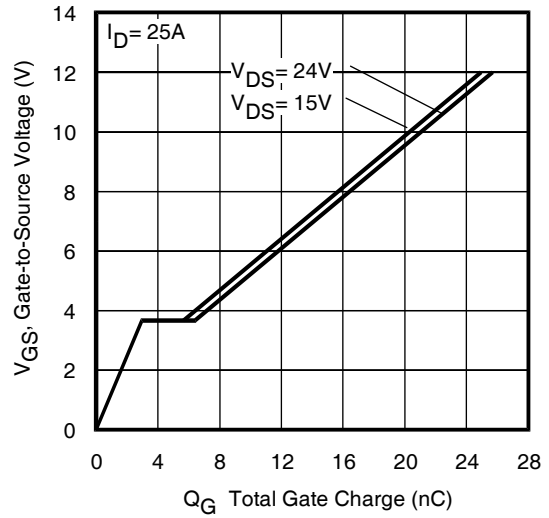


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

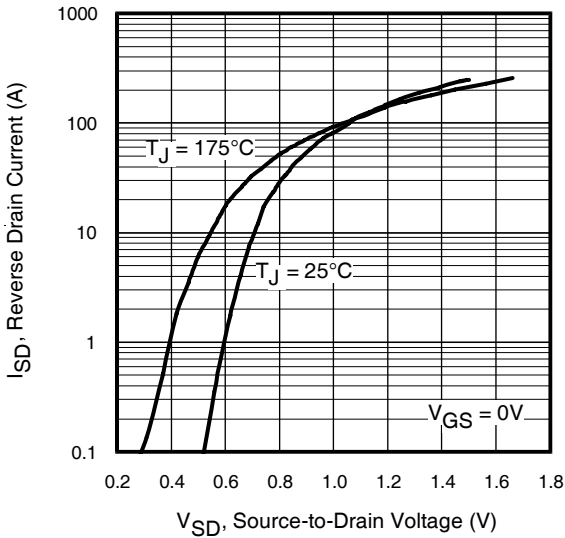


Fig 7. Typical Source-Drain Diode Forward Voltage

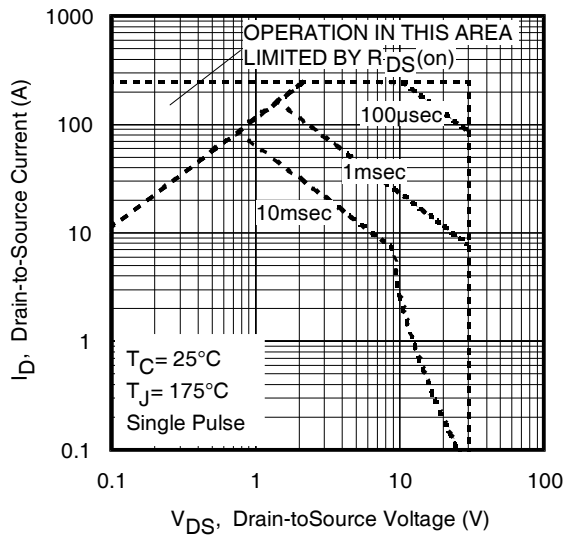


Fig 8. Maximum Safe Operating Area

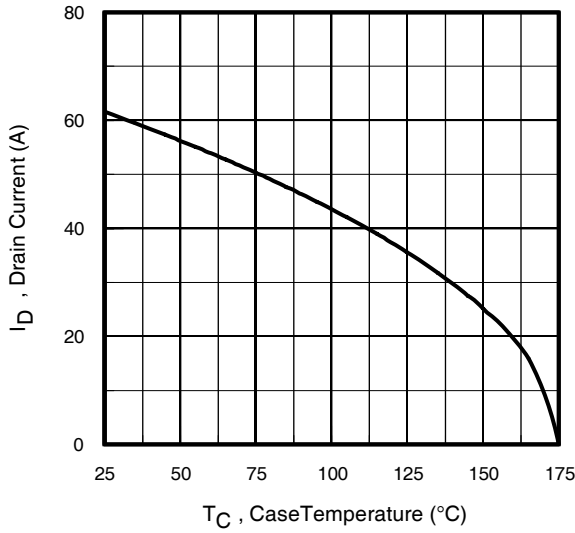


Fig 9. Maximum Drain Current vs. Case Temperature

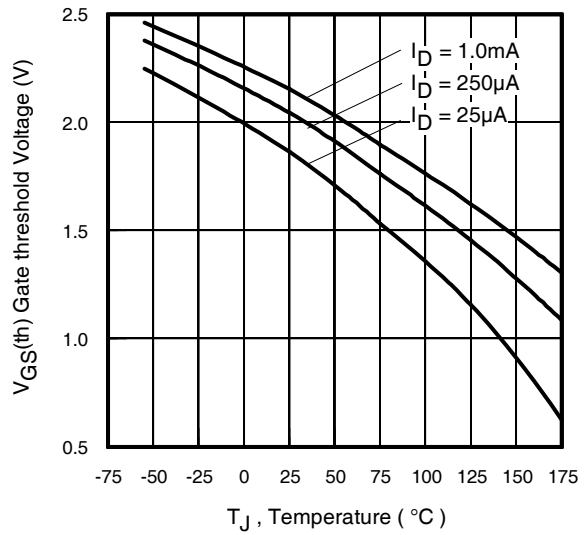


Fig 10. Threshold Voltage vs. Temperature

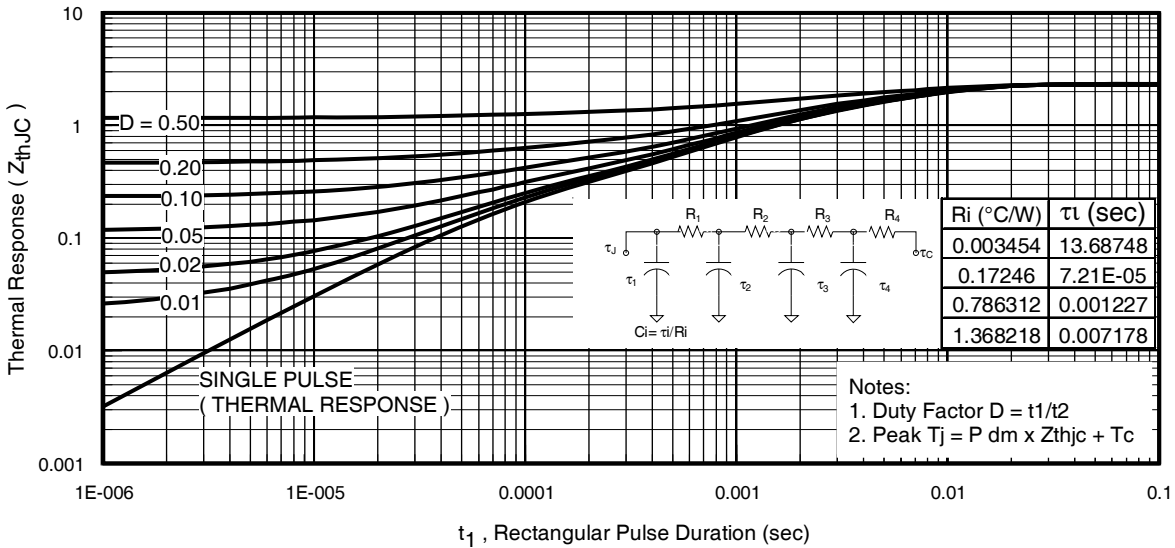


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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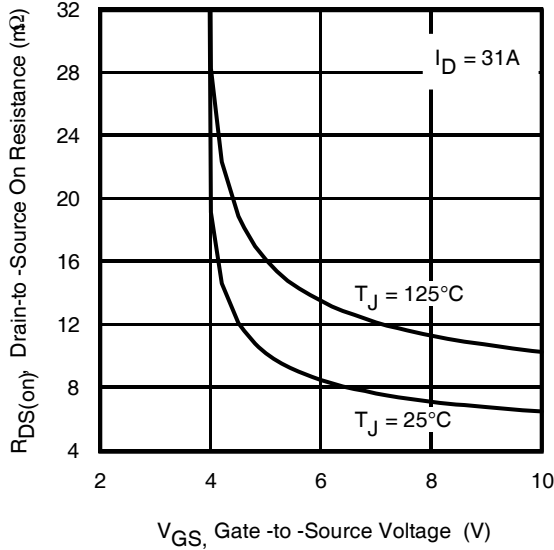


Fig 12. On-Resistance vs. Gate Voltage

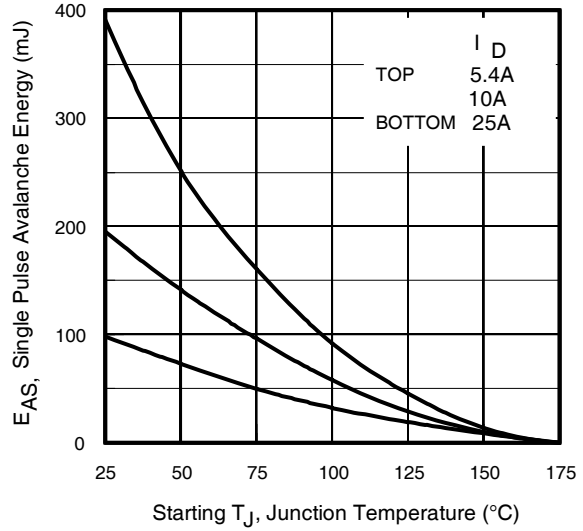


Fig 13a. Maximum Avalanche Energy vs. Drain Current

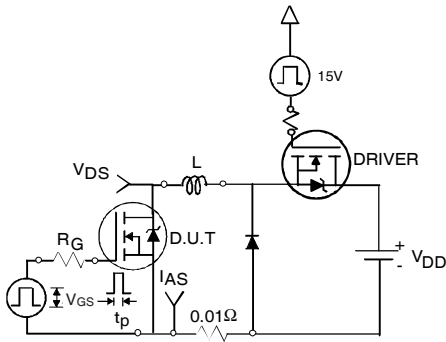


Fig 13b. Unclamped Inductive Test Circuit

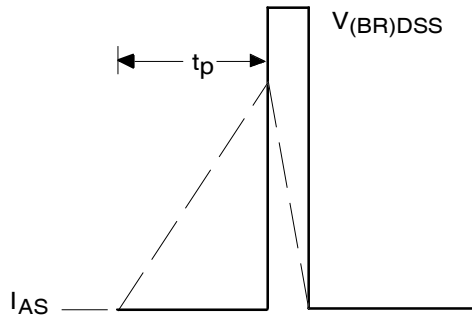


Fig 13c. Unclamped Inductive Waveforms

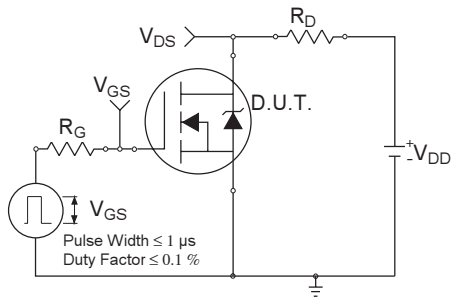


Fig 14a. Switching Time Test Circuit

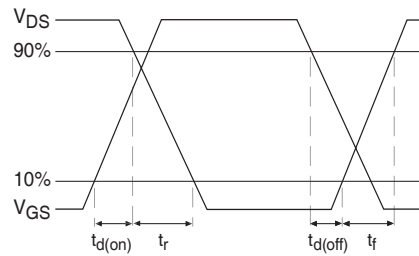


Fig 14b. Switching Time Waveforms

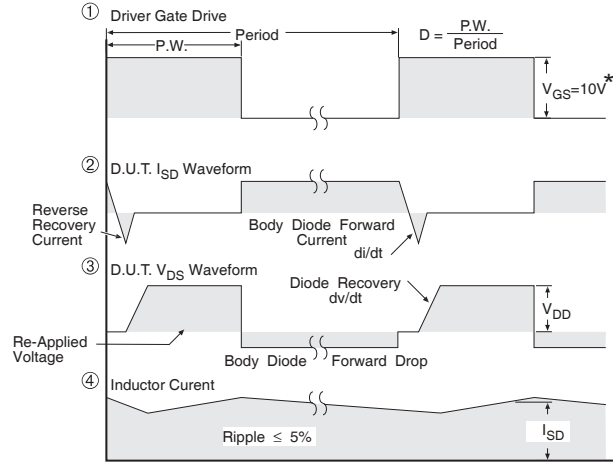
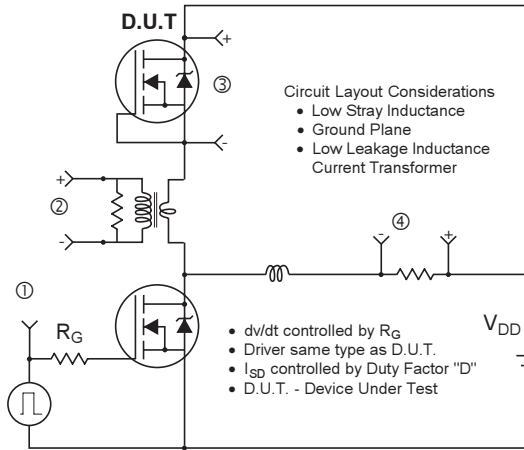


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

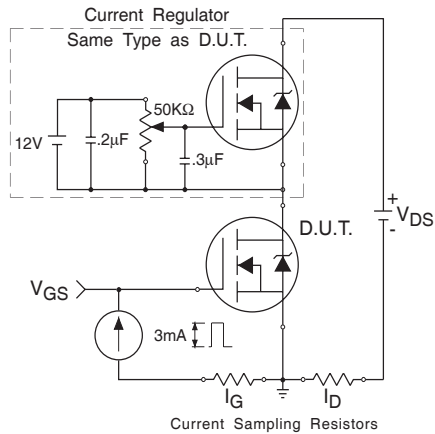


Fig 16a. Gate Charge Test Circuit

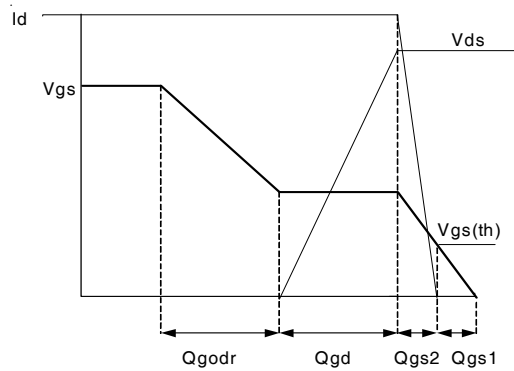
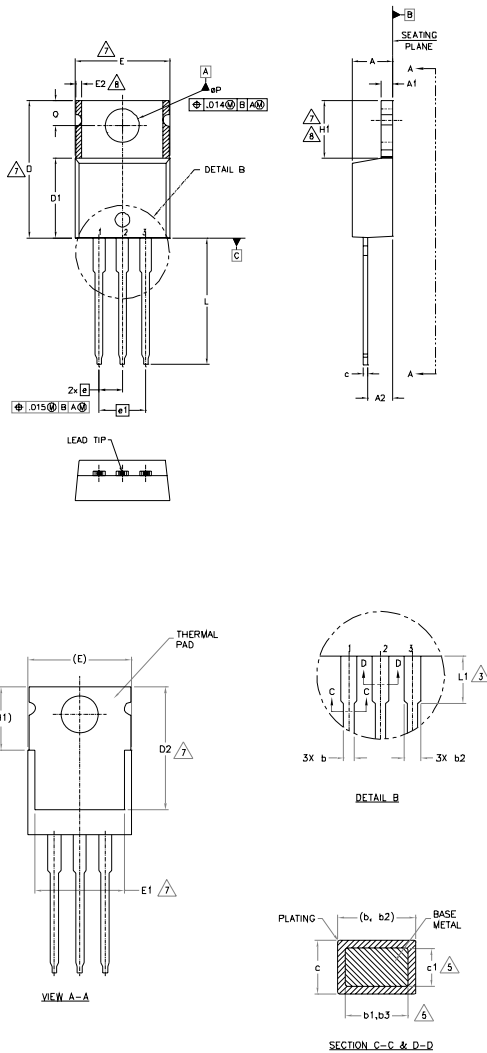


Fig 16b. Gate Charge Waveform

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TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.356	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

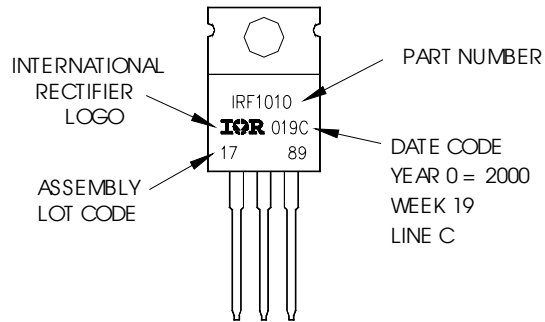
TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position
indicates "Lead - Free"



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.32\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 25\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑤ R_θ is measured at T_J approximately 90°C .

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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